



**THE DATASHEET OF  
X0402DF 1AA2**



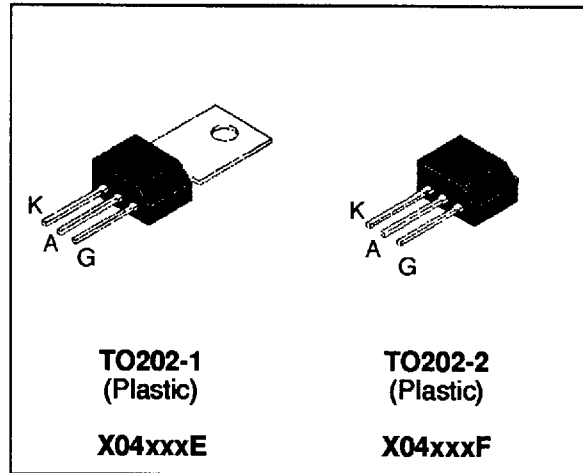
**SENSITIVE GATE SCR**

**FEATURES**

- $I_{T(RMS)} = 4A$
- $V_{DRM} = 200V$  to  $800V$
- Low  $I_{GT} < 200\mu A$

**DESCRIPTION**

The X04xxxE/F series of SCRs uses a high performance TOP GLASS PNP technology. These parts are intended for general purpose applications where low gate sensitivity is required.



**ABSOLUTE RATINGS** (limiting values)

| Symbol             | Parameter   |                              | Value                      | Unit       |
|--------------------|---|------------------------------|----------------------------|------------|
| $I_{T(RMS)}$       | RMS on-state current<br>(180° conduction angle)   | X04xxxE/F $T_c = 90^\circ C$ | 4                          | A          |
|                    |   | X04xxxF $T_a = 25^\circ C$   | 1.35                       |            |
| $I_{T(AV)}$        | Mean on-state current<br>(180° conduction angle)  | X04xxxE/F $T_c = 90^\circ C$ | 2.5                        | A          |
|                    |   | X04xxxF $T_a = 25^\circ C$   | 0.9                        |            |
| $I_{TSM}$          | Non repetitive surge peak on-state current<br>( $T_j$ initial = $25^\circ C$ )          | $t_p = 8.3$ ms               | 33                         | A          |
|                    |   | $t_p = 10$ ms                | 30                         |            |
| $I^2t$             | $I^2t$ Value for fusing   | $t_p = 10$ ms                | 4.5                        | $A^2s$     |
| $di/dt$            | Critical rate of rise of on-state current<br>$I_G = 10$ mA $di_G/dt = 0.1$ A/ $\mu s$ . |                              | 50                         | A/ $\mu s$ |
| $T_{stg}$<br>$T_j$ | Storage and operating junction temperature range  |                              | - 40, + 150<br>- 40, + 125 | $^\circ C$ |
| $T_l$              | Maximum lead temperature for soldering during 10s at 4.5mm from case                    |                              | 260                        | $^\circ C$ |

| Symbol                 | Parameter  | Voltage |     |     |     | Unit |
|------------------------|--|---------|-----|-----|-----|------|
|                        |  | B       | D   | M   | N   |      |
| $V_{DRM}$<br>$V_{RRM}$ | Repetitive peak off-state voltage<br>$T_j = 125^\circ C$ $R_{GK} = 1K\Omega$ | 200     | 400 | 600 | 800 | V    |

# X04xxxE/F

## THERMAL RESISTANCES

| Symbol   | Parameter               |         | Value | Unit |
|----------|-------------------------|---------|-------|------|
| Rth(j-a) | Junction to ambient     | X04xxxE | 80    | °C/W |
|          |                         | X04xxxF | 100   |      |
| Rth(j-c) | Junction to case for DC |         | 7.5   | °C/W |

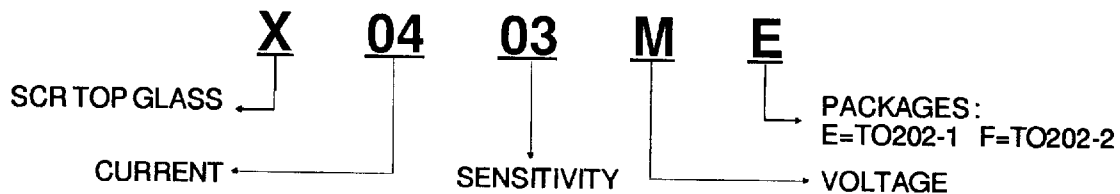
## GATE CHARACTERISTICS (maximum values)

$P_G (AV) = 0.2 \text{ W}$   $P_{GM} = 3 \text{ W}$  ( $t_p = 20 \mu\text{s}$ )  $I_{GM} = 1.2 \text{ A}$  ( $t_p = 20 \mu\text{s}$ )

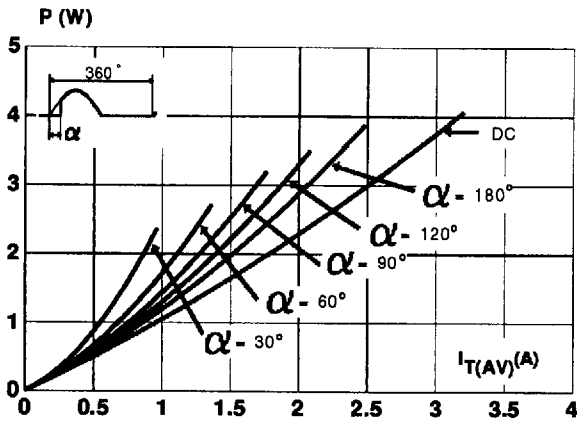
## ELECTRICAL CHARACTERISTICS

| Symbol                               | Test Conditions  |                        |     |     | Sensitivity |    |      | Unit |
|--------------------------------------|--|------------------------|-----|-----|-------------|----|------|------|
|                                      |  |                        |     |     | 02          | 03 | 05   |      |
| I <sub>GT</sub>                      | V <sub>D</sub> =12V (DC) R <sub>L</sub> =140Ω  | T <sub>j</sub> = 25°C  | MIN |     | 20          | 20 | μA   |      |
|                                      |  |                        | MAX | 200 | 200         | 50 |      |      |
| V <sub>GT</sub>                      | V <sub>D</sub> =12V (DC) R <sub>L</sub> =140Ω  | T <sub>j</sub> = 25°C  | MAX | 0.8 |             |    | V    |      |
| V <sub>GD</sub>                      | V <sub>D</sub> =V <sub>DRM</sub> R <sub>L</sub> =3.3kΩ<br>R <sub>GK</sub> = 1 KΩ   | T <sub>j</sub> = 125°C | MIN | 0.1 |             |    | V    |      |
| V <sub>RGM</sub>                     | I <sub>RG</sub> = 10μA   | T <sub>j</sub> = 25°C  | MIN | 8   |             |    | V    |      |
| t <sub>gd</sub>                      | V <sub>D</sub> =V <sub>DRM</sub> I <sub>TM</sub> = 3 x I <sub>T(AV)</sub><br>dI <sub>G</sub> /dt = 0.1A/μs I <sub>G</sub> = 10mA   | T <sub>j</sub> = 25°C  | MAX | 2   |             |    | μs   |      |
| I <sub>H</sub>                       | I <sub>T</sub> = 50mA R <sub>GK</sub> = 1 KΩ   | T <sub>j</sub> = 25°C  | MAX | 5   |             |    | mA   |      |
| I <sub>L</sub>                       | I <sub>G</sub> =1mA R <sub>GK</sub> = 1 KΩ   | T <sub>j</sub> = 25°C  | MAX | 6   |             |    | mA   |      |
| V <sub>TM</sub>                      | I <sub>TM</sub> = 8A t <sub>p</sub> = 380μs  | T <sub>j</sub> = 25°C  | MAX | 1.8 |             |    | V    |      |
| I <sub>DRM</sub><br>I <sub>RRM</sub> | V <sub>D</sub> = V <sub>DRM</sub> R <sub>GK</sub> = 1 KΩ<br>V <sub>R</sub> = V <sub>RRM</sub>  | T <sub>j</sub> = 25°C  | MAX | 5   |             |    | μA   |      |
|                                      |  | T <sub>j</sub> = 110°C | MAX | 200 |             |    |      |      |
| dV/dt                                | V <sub>D</sub> =67%V <sub>DRM</sub> R <sub>GK</sub> = 1 KΩ   | T <sub>j</sub> = 110°C | MIN |     |             | 10 | V/μs |      |
|                                      |  |                        | TYP | 15  | 20          | 15 |      |      |
| t <sub>q</sub>                       | I <sub>TM</sub> = 3 x I <sub>T(AV)</sub> V <sub>R</sub> =35V<br>dI/dt=10A/μs t <sub>p</sub> =100μs<br>dV/dt=2V/μs<br>V <sub>D</sub> = 67%V <sub>DRM</sub> R <sub>GK</sub> = 1 KΩ | T <sub>j</sub> = 110°C | MAX | 50  |             |    | μs   |      |

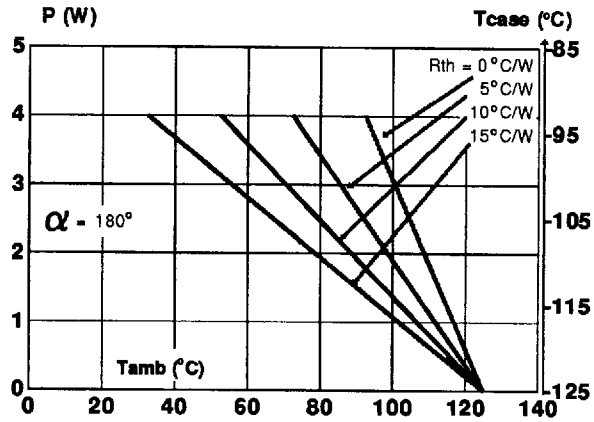
## ORDERING INFORMATION



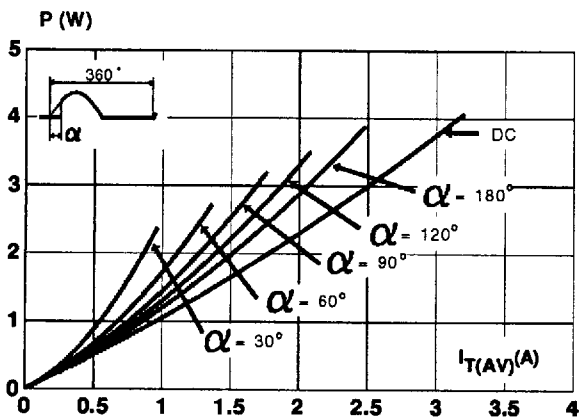
**Fig.1 :** Maximum average power dissipation versus average on-state current (TO202-1).



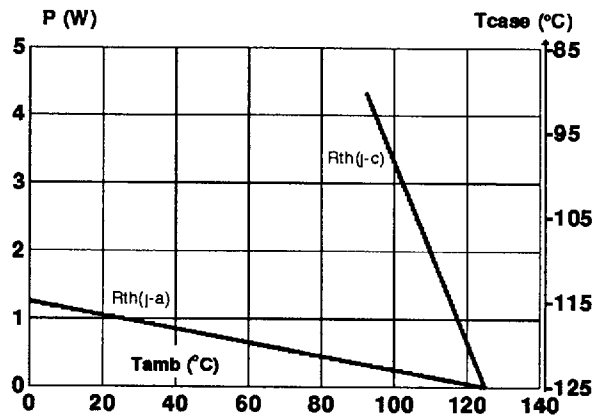
**Fig.2 :** Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tcase) for different thermal resistances heatsink + contact (TO202-1).



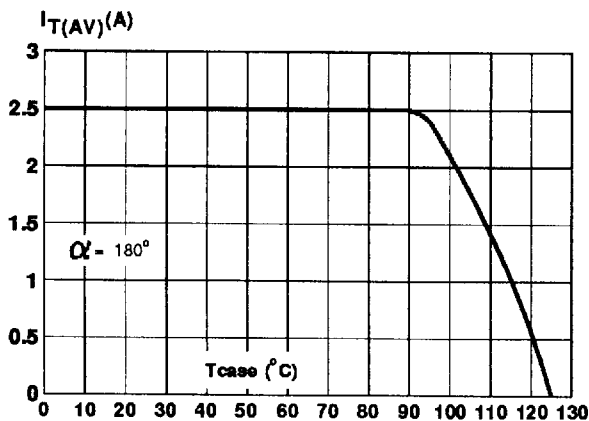
**Fig.3 :** Maximum average power dissipation versus average on-state current (TO202-2).



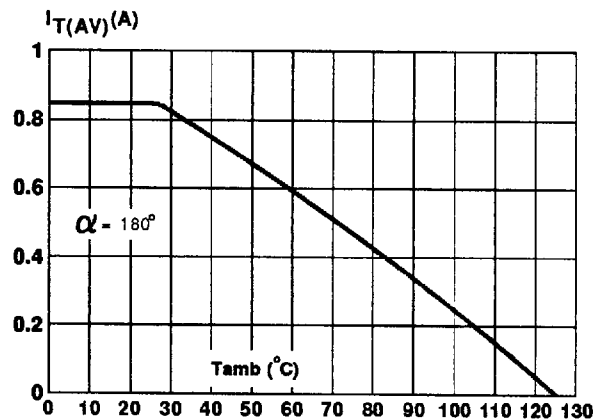
**Fig.4 :** Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tcase) (TO202-2).



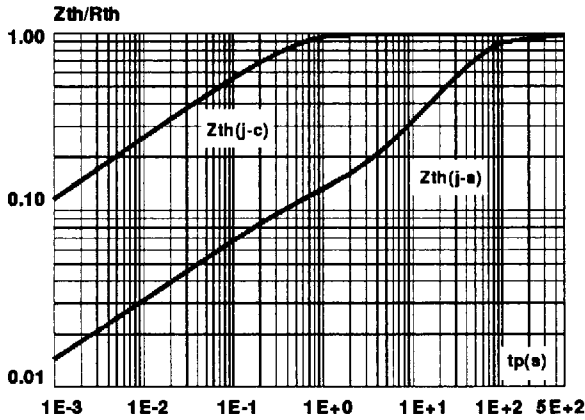
**Fig.5 :** Average on-state current versus case temperature (TO202-1).



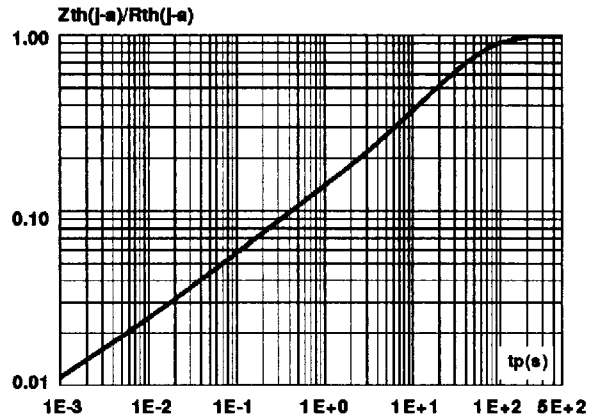
**Fig.6 :** Average on-state current versus case temperature (TO202-2).



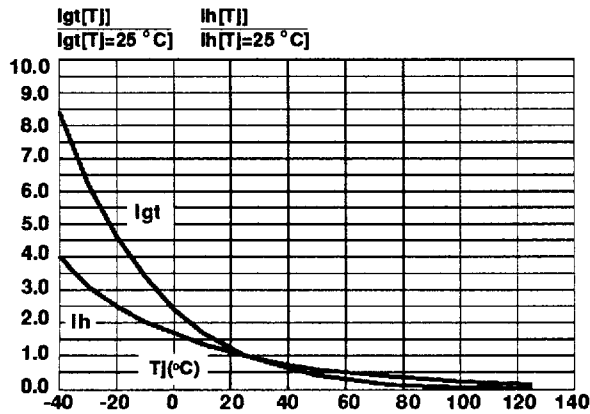
**Fig.7 :** Relative variation of thermal impedance versus pulse duration (TO202-1).



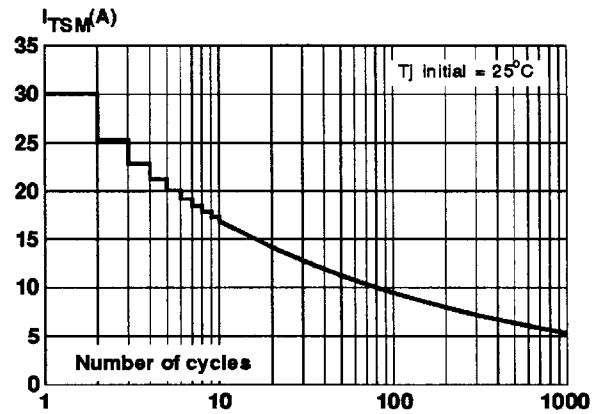
**Fig.8 :** Relative variation of thermal impedance junction to ambient versus pulse duration (TO202-2).



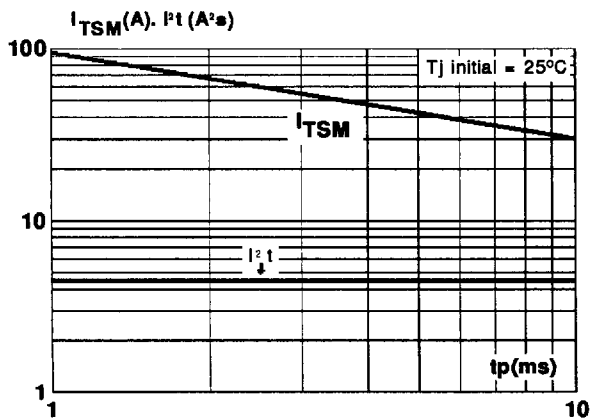
**Fig.9 :** Relative variation of gate trigger current and holding current versus junction temperature.



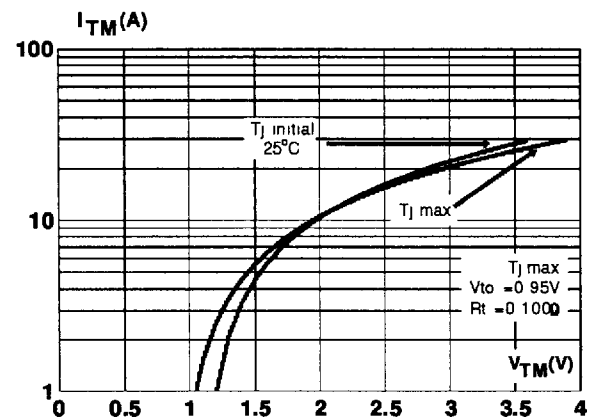
**Fig.10 :** Non repetitive surge peak on-state current versus number of cycles.



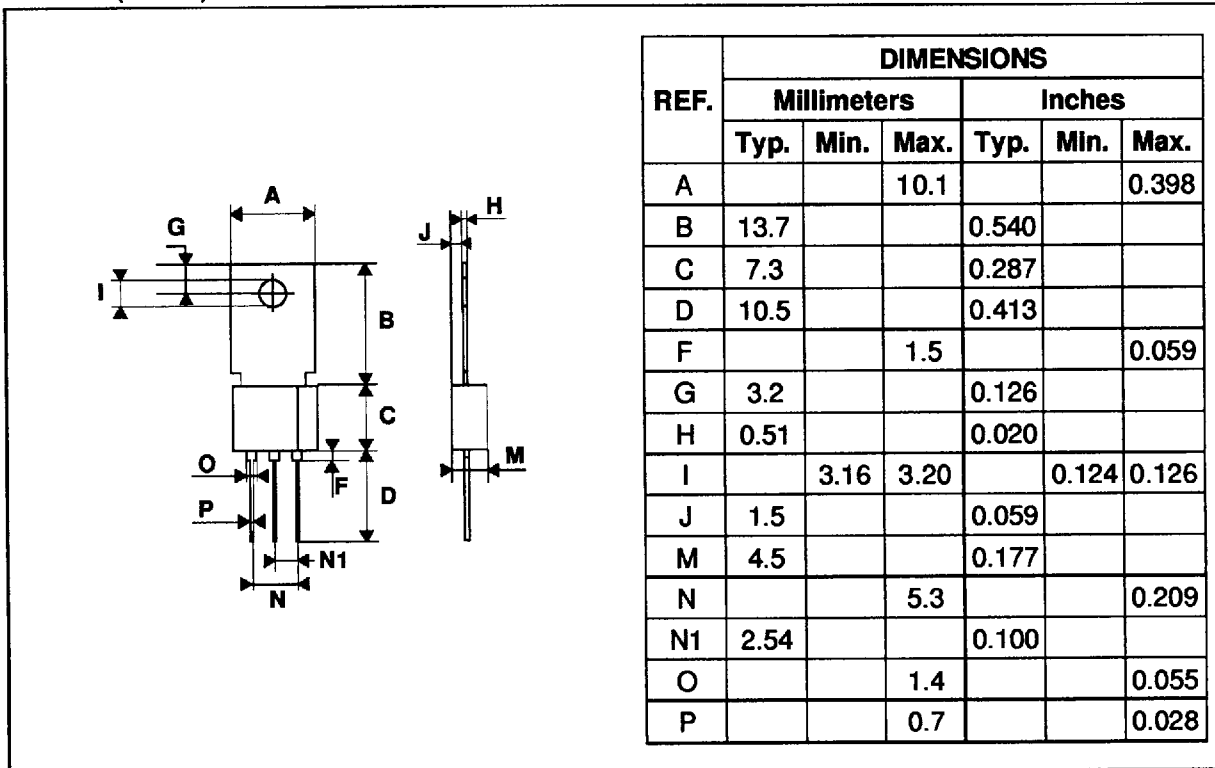
**Fig.11 :** Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $tp \leq 10ms$ , and corresponding value of  $I^2t$ .



**Fig.12 :** On-state characteristics (maximum values).



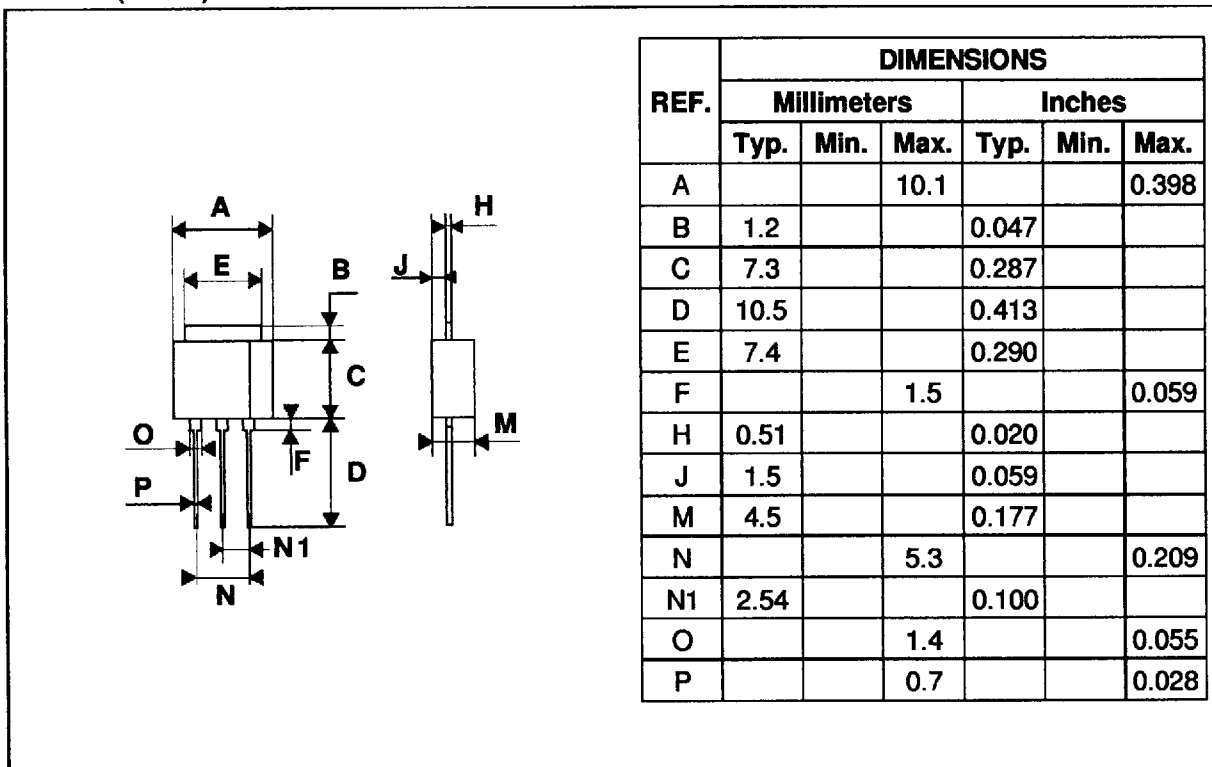
**PACKAGE MECHANICAL DATA**  
TO202-1 (Plastic)



Marking : type number  
Weight : 1.4 g

X04xxxE/F

**PACKAGE MECHANICAL DATA**  
TO202-2 (Plastic)



Marking : type number  
Weight : 1.0 g

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